

Table of Contents

Committees

Sponsors

Preface

Overview

Chapter 1: SiC Bulk Growth

1.1 Bulk Growth of 4H- and 6H-SiC

Growth of Crack-Free 100mm-Diameter 4H-SiC Crystals with Low Micropipe Densities

M. Nakabayashi, T. Fujimoto, M. Katsuno, N. Ohtani, H. Tsuge, H. Yashiro, T. Aigo, T. Hoshino, H. Hirano and K. Tatsumi

3

100 mm 4HN-SiC Wafers with Zero Micropipe Density

R.T. Leonard, Y. Khlebnikov, A.R. Powell, C. Basceri, M.F. Brady, I. Khlebnikov, J.R. Jenny, D.P. Malta, M.J. Paisley, V.F. Tsvetkov, R. Zilli, E. Deyneka, H.M. Hobgood, V. Balakrishna and C.H. Carter Jr.

7

Investigations on Polytype Stability and Dislocation Formation in 4H-SiC Grown by PVT

E. Schmitt, T.L. Straubinger, M. Rasp, M. Vogel and A. Wohlfart

11

Growth of 6H-SiC Single Crystals under Quasi-Equilibrium Conditions

E. Tymicki, K. Graszka, W. Hofman, R. Diduszko and R. Bożek

15

Aluminum P-Type Doping of Bulk SiC Single Crystals by Tri-Methyl-Aluminum

P. Hens, U. Künecke and P.J. Wellmann

19

Growth on Rhombohedral (01-1n) Plane: An Alternative for Preparation of High Quality Bulk SiC Crystals

O. Filip, B.M. Epelbaum, J. Li, M. Bickermann, X.G. Xu and A. Winnacker

23

Bulk SiC Crystal Growth at Constant Growth Rate Utilizing a New Design of Resistive Furnace

E.Y. Tupitsyn, A. Galyukov, M.V. Bogdanov, A. Kulik, M.S. Ramm, Y. Makarov and T.S. Sudarshan

27

Application of 6H to 4H Polytype Conversion to Effective Reduction of Micropipes in 4H SiC Crystals

K. Graszka and E. Tymicki

31

Status of Large Diameter SiC Single Crystals at II-VI

A.K. Gupta, I. Zwieback, A.E. Souzis, M. Yoganathan and T. Anderson

35

Occurrence of Polytype Transformation during Nitrogen Doping of SiC Bulk Wafer

J. Chen, S.C. Lien, Y.C. Shin, Z.C. Feng, C.H. Kuan, J.H. Zhao, J.H. Zhao and W.J. Lu

39

The Observation and Explanation of Electricity Switch Phenomena in PVT Grown SiC Bulk

J.M. Hao, L.J. Wang, B. Fen, X.Q. Wang, Y. Hong, D.L. Meng, J.M. Guo and R.Y. Yan

43

Simulation Study for HTCVD of SiC Using First-Principles Calculation and Thermo-Fluid Analysis

Y. Kito, E. Makino, K. Inaba, N. Hosokawa, H. Hiramatsu, J. Hasegawa, S. Onda, H. Tsuboi, H. Takaba and A. Miyamoto

47

Computational Analysis of SiC HTCVD from Silicon Tetrachloride and Propane

Y. Makarov, R.A. Talalaev, A.N. Vorob'ev, M.S. Ramm and M.V. Bogdanov

51

1.2 Bulk Growth of 2H- and 3C-SiC

Growth of 2H-SiC Single Crystals in a C-Li-Si Ternary Melt System

M. Imade, T. Ogura, M. Uemura, F. Kawamura, M. Yoshimura, Y. Kitaoka, Y. Mori, T. Sasaki, M. Yamazaki and S. Suwabe

55

Solution Growth of SiC Crystals in Si-Ti and Si-Ge-Ti Solvents

R. Tanaka, K. Seki, S. Komiyama, T. Ujihara and Y. Takeda

59

Stability Growth Condition for 3C-SiC Crystals by Solution Technique

T. Ujihara, R. Maekawa, R. Tanaka, K. Sasaki, K. Kuroda and Y. Takeda

63

Structural Characterization of CF-PVT Grown Bulk 3C-SiC	
A. Mantzari, F. Mercier, M. Soueidan, D. Chaussende, G. Ferro and E.K. Polychroniadis	67
Comparative Study of Differently Grown 3C-SiC Single Crystals with Birefringence Microscopy	
D. Chaussende, F. Mercier, R. Madar and M. Pons	71

Chapter 2: SiC Epitaxial Growth

2.1 Milestones

SiC Epitaxial Growth on Multiple 100-mm Wafers and its Application to Power-Switching Devices	
A.A. Burk, M.J. O'Loughlin, J.J. Sumakeris, C. Hallin, E. Berkman, V. Balakrishna, J. Young, L. Garrett, K.G. Irvine, A.R. Powell, Y. Khlebnikov, R.T. Leonard, C. Basceri, B.A. Hull and A.K. Agarwal	77
Silicon Carbide Growth:C/Si Ratio Evaluation and Modeling	
M. Pons, S.I. Nishizawa, P.J. Wellmann, E. Blanquet, D. Chaussende, J.M. Dedulle and R. Madar	83
Challenges for Improving the Crystal Quality of 3C-SiC Verified with MOSFET Performance	
H. Nagasawa, K. Yagi, T. Kawahara, N. Hatta, M. Abe, A. Schöner, M. Bakowski, P. Ericsson and G. Pensl	89

2.2 Homoepitaxial Growth

Advances in Multi- and Single-Wafer SiC Epitaxy for the Production and Development of Power Diodes	
C. Hecht, B. Thomas, R.A. Stein and P. Friedrichs	95
Extremely Uniform, High Quality SiC Epitaxy on 100-mm Substrates	
J.J. Sumakeris, J. Henning, M.J. O'Loughlin, S. Sriram and V. Balakrishna	99
High Quality Epitaxial Growth on 4° Off-Axis 4H SiC with Addition of HCl	
J. Zhang, J. Mazzola, S.G. Sunkari, G. Stewart, P.B. Klein, R.M. Ward, E.R. Glaser, K.K. Lew, D.K. Gaskill, I. Sankin, V. Bondarenko, D. Null, D.C. Sheridan and M.S. Mazzola	103
Homoepitaxial Growth of 4H-SiC on On-Axis Si-Face Substrates Using Chloride-Based CVD	
S. Leone, H. Pedersen, A. Henry, O. Kordina and E. Janzén	107
Development of a High Rate 4H-SiC Epitaxial Growth Technique Achieving Large-Area Uniformity	
M. Ito, L. Storasta and H. Tsuchida	111
Very High Growth Rate of 4H-SiC Using MTS as Chloride-Based Precursor	
H. Pedersen, S. Leone, A. Henry, F.C. Beyer, V. Darakchieva and E. Janzén	115
Development of a Practical High-Rate CVD System	
Y. Ishida, T. Takahashi, H. Okumura, K. Arai and S. Yoshida	119
SiC-4H Epitaxial Layer Growth by Trichlorosilane (TCS) as Silicon Precursor at Very High Growth Rate	
F. La Via, G. Izzo, M. Mauceri, G. Pistone, G. Condorelli, L.M.S. Perdicaro, G. Abbondanza, F. Portuese, G. Galvagno, S. Di Franco, L. Calcagno, G. Foti, G.L. Valente and D. Crippa	123
Thin SiC-4H Epitaxial Layer Growth by Trichlorosilane (TCS) as Silicon Precursor with Very Abrupt Junctions	
G. Condorelli, M. Mauceri, G. Pistone, L.M.S. Perdicaro, G. Abbondanza, F. Portuese, G.L. Valente, D. Crippa, F. Giannazzo and F. La Via	127
Multi-Level Simulation Study of Crystal Growth and Defect Formation Processes in SiC	
H. Takaba, A. Sagawa, M. Sato, S. Ouchi, Y. Yoshida, Y. Hayashi, E. Sato, K. Inaba, R. Sahnoun, M. Koyama, H. Tsuboi, N. Hatakeyama, A. Endou, M. Kubo, C.A. Del Carpio, Y. Kito, E. Makino, N. Hosokawa, J. Hasegawa, S. Onda and A. Miyamoto	131
Theoretical Monte Carlo Study of the Formation and Evolution of Defects in the Homoepitaxial Growth of SiC	
M. Camarda, A. La Magna, P. Fiorenza, G. Izzo and F. La Via	135
Investigation of Triangular Defects in 4H-SiC 4° Off Cut (0001) Si Face Epilayers Grown by CVD	
A. Shrivastava, P.G. Muzykov, B. Pearman, S.M. Angel and T.S. Sudarshan	139

Influence of Substrate Preparation and Epitaxial Growth Parameters on the Dislocation Densities in 4H-SiC Epitaxial Layers	
B. Kallinger, B. Thomas and J. Friedrich	143
<i>In Situ</i> Boron and Aluminum Doping and Their Memory Effects in 4H-SiC Homoepitaxial Layers Grown by Hot-Wall LPCVD	
G.S. Sun, Y.M. Zhao, L. Wang, L. Wang, W.S. Zhao, X.F. Liu, G. Ji and Y.P. Zeng	147
Homoepitaxial Growth of 4H-SiC by Hot-Wall CVD Using BTMSM	
H.S. Seo, H.G. Song, J.H. Moon, J.H. Yim, M.S. Oh, J.H. Lee, Y.J. Choi and H.J. Kim	151
Effect of Substrates Thermal Etching on CVD Growth of Epitaxial Silicon Carbide Layers	
W. Strupiński, K. Kościwicz, J. Weyher and A.R. Olszyna	155
Nitrogen Doping in Low-Temperature Halo-Carbon Homoepitaxial Growth of SiC	
K. Chindanon, H.D. Lin, G. Melnychuk and Y. Koshka	159
Local-Loading Effect in Low-Temperature Selective Epitaxial Growth of 4H-SiC by Halo-Carbon Method	
H. Das, B. Krishnan, G. Melnychuk and Y. Koshka	163
Micropipe Dissociation through Thick n^+ Buffer Layer Growth	
M.F. MacMillan, E. Sanchez, M. Dudley, Y. Chen and M.J. Loboda	167
Growth Mechanism and 2D Aluminum Dopant Distribution of Embedded Trench 4H-SiC Region	
N. Sugiyama, Y. Takeuchi, M. Kataoka, A. Schöner and R.K. Malhan	171
<i>In Situ</i> Nitrogen and Aluminum Doping in Migration Enhanced Embedded Epitaxial Growth of 4H-SiC	
A. Schöner, N. Sugiyama, Y. Takeuchi and R.K. Malhan	175
Solution Growth of Off-Axis 4H-SiC for Power Device Application	
R. Hattori, K. Kusunoki, N. Yashiro and K. Kamei	179
Epitaxial TaC Films for the Selective Area Growth of SiC	
K.A. Jones, T.S. Zheleva, R.D. Vispute, S.S. Hullavarad, M. Ervin and S. Dhar	183

2.3 Heteropolytypic and Heteroepitaxial Growth

Solution Growth of 3C-SiC on 6H-SiC Using Si Solvent under N_2-He Atmosphere	
K. Kusunoki, K. Kamei, N. Yashiro, T. Tanaka and A. Yauchi	187
Solution Growth of 3C-SiC Single Crystals by Cold Crucible Technique	
T. Tanaka, N. Yashiro, K. Kusunoki, K. Kamei and A. Yauchi	191
Growth Mechanism of 3C-SiC Heteroepitaxial Layers on α-SiC by VLS	
G. Ferro, M. Soueidan, O. Kim-Hak, J. Dazord, F. Cauwet and B. Nsouli	195
Growth Kinetics of 3C-SiC on α-SiC by VLS	
M. Soueidan, O. Kim-Hak, G. Ferro, N. Habka and B. Nsouli	199
3C-SiC Islands Formation on 6H-SiC(0001) Substrate from a Liquid Phase	
O. Kim-Hak, M. Soueidan, G. Ferro, O. Dezellus, A. Andreadou, D. Carole, E.K. Polychroniadis and J.C. Viala	203
Strain in 3C-SiC Heteroepitaxial Layers Grown on (100) and (111) Oriented Silicon Substrates	
M. Zielinski, M. Portail, T. Chassagne and Y. Cordier	207
Growth of 3C-SiC on Si: Influence of Process Pressure	
A. Severino, C.L. Frewin, R. Anzalone, C. Bongiorno, P. Fiorenza, G. D'Arrigo, F. Giannazzo, G. Foti, F. La Via and S.E. Saddow	211
Void Formation in Differently Oriented Si in the Early Stage of SiC Growth	
A. Severino, C. Bongiorno, R. Anzalone, G. Abbondanza, M. Mauceri, G. Condorelli, G. Foti and F. La Via	215
3C-SiC on Si Substrates Using Pendeo-Epitaxial Growth	
B.C. Kim and M.A. Capano	219
Influence of Growth Parameters on the Residual Strain in 3C-SiC Epitaxial Layers on (001) Silicon	
G. Wagner, J. Schwarzkopf, M. Schmidbauer and R. Fornari	223
Island Formation of SiC Film on Striated Si(001) Substrates	
Y. Kato and K. Sakumoto	227

Structural and Morphological Characterization of 3C-SiC Films Grown on (111), (211) and (100) Silicon Substrates	
M. Portail, M. Nemoz, M. Zielinski and T. Chassagne	231
Heteroepitaxial Growth of 3C-SiC on Si (111) at Low Substrate Temperature by Plasma Assisted CVD	
H. Shimizu and A. Kato	235
Buckling Stabilization and Stress Reduction in SiC on Si by i-FLASiC Processing	
A. Andreadou, J. Pezoldt, C. Förster, E.K. Polychroniadis, M. Voelskow and W. Skorupa	239
3C-SiC Heteroepitaxy on (100), (111) and (110) Si Using Trichlorosilane (TCS) as the Silicon Precursor.	
R. Anzalone, A. Severino, G. D'Arrigo, C. Bongiorno, P. Fiorenza, G. Foti, G. Condorelli, M. Mauceri, G. Abbondanza and F. La Via	243
Hetero-Epitaxial Growth of 3C-SiC with Smooth Surface on Si(001) Using Acetylene Gas	
Y. Hirabayashi, S. Kaneko and K. Akiyama	247
Heteroepitaxial Growth of 3C-SiC on Si (111) Substrate Using AlN as a Buffer Layer	
Y.M. Zhao, G.S. Sun, X.F. Liu, J.Y. Li, W.S. Zhao, L. Wang, J.M. Li and Y.P. Zeng	251
Characteristics of Polycrystalline 3C-SiC Thin Films Grown on AlN Buffer Layer by CVD	
G.S. Chung and K.S. Kim	255

Chapter 3: Physical Properties and Characterization of SiC

3.1 Milestones

Aspects of Dislocation Behavior in SiC	
M. Dudley, Y. Chen, X.R. Huang and R.H. Ma	261
Investigation of Defect Formation in 4H-SiC(0001) and (000-1) Epitaxy	
H. Tsuchida, I. Kamata and M. Nagano	267
Temperature Dependence of Shockley Stacking Fault Expansion and Contraction in 4H-SiC p-i-n Diodes	
J.D. Caldwell, R.E. Stahlbush, O.J. Glembocki, K.D. Hobart, K.X. Liu and M.J. Tadjer	273
EPR Identification of Defects and Impurities in SiC: To be Decisive	
J. Isoya, T. Umeda, N. Mizuochi, N.T. Son, E. Janzén and T. Ohshima	279
Defects Identified in SiC and Their Implications	
M. Bockstedte, A. Marini, A. Gali, O. Pankratov and A. Rubio	285
Atomic and Electronic Structure of the (2×1) and c(2×2) 4H-SiC(1-102) Surfaces	
C. Virojanadara, M. Hetzel, L.I. Johansson, W.J. Choyke and U. Starke	291

3.2 Extended Defects

Sense Determination of c-Axis Screw Dislocations in 4H-SiC	
Y. Chen, X.R. Huang, G. Dhanaraj, M. Dudley, E. Sanchez and M.F. MacMillan	297
Studies of the Distribution of Elementary Threading Screw Dislocations in 4H Silicon Carbide Wafer	
Y. Chen, N. Zhang, X.R. Huang, D.R. Black and M. Dudley	301
High-Resolution Topography Analysis on Threading Edge Dislocations in 4H-SiC Epilayers	
I. Kamata, M. Nagano, H. Tsuchida, Y. Chen and M. Dudley	305
Observation of Misfit Dislocations Introduced by Epi-Layer Growth on 4H-SiC	
H. Matsuhata, H. Yamaguchi, I. Nagai, T. Ohno, R. Kosugi and A. Kinoshita	309
Dislocation Contrast of 4H-SiC in X-Ray Topography under Weak-Beam Condition	
H. Yamaguchi, H. Matsuhata and I. Nagai	313
Evolution of Basal Plane Dislocations during 4H-SiC Epitaxial Growth	
R.E. Stahlbush, B.L. VanMil, K.X. Liu, K.K. Lew, R.L. Myers-Ward, D.K. Gaskill, C.R. Eddy, X. Zhang and M. Skowronski	317
Contrast of Basal Plane and Threading Edge Dislocations in 4H-SiC by X-Ray Topography in Grazing Incidence Geometry	
H. Matsuhata, H. Yamaguchi, I. Nagai, T. Ohno, R. Kosugi and A. Kinoshita	321
Slip of Basal Plane Dislocations in 4H-SiC Epitaxy	
T. Ohno	325

Pair-Generation of the Basal-Plane-Dislocation during Crystal Growth of SiC T. Nishiguchi, T. Furusho, T. Isshiki, K. Nishio, H. Shiomi and S. Nishino	329
Characterization of Dislocations and Micropipes in 4H n⁺ SiC Substrates P. Wu, M. Yoganathan, I. Zwieback, Y. Chen and M. Dudley	333
Raman Scattering Study of Stress Distribution around Dislocation in SiC D. Matsuoka, H. Yamamoto, S. Nishino, N. Hasuike, K. Kisoda and H. Harima	337
Stacking Fault Formation in Highly Nitrogen-Doped 4H-SiC Substrates with Different Surface Preparation Conditions M. Katsuno, M. Nakabayashi, T. Fujimoto, N. Ohtani, H. Yashiro, H. Tsuge, T. Aigo, T. Hoshino and K. Tatsumi	341
Differences in Emission Spectra of Dislocations in 4H-SiC Epitaxial Layers K.X. Liu, X. Zhang, R.E. Stahlbush, M. Skowronski and J.D. Caldwell	345
Expansion of Stacking Faults in 4H-SiC Epitaxial Layer under Laser Light Excitation during Room Temperature Photoluminescence Mapping N. Hoshino, M. Tajima, M. Naitoh, E. Okuno and S. Onda	349
Expansion of Stacking Faults by Electron-Beam Irradiation in 4H-SiC Diode Structure R. Sugie, M. Yoshikawa, S. Harada and Y. Namikawa	353
Synchrotron X-Ray Topographic Studies of Recombination Activated Shockley Partial Dislocations in 4H-Silicon Carbide Epitaxial Layers Y. Chen, X.R. Huang, N. Zhang, M. Dudley, J.D. Caldwell, K.X. Liu and R.E. Stahlbush	357
X-Ray Rocking Curve Characterization of SiC Substrates M. Yoganathan, P. Wu and I. Zwieback	361
TEM Observation of the Polytype Transformation of Bulk SiC Ingot M. Aoki, M. Miyazaki, T. Nishiguchi, H. Kinoshita and M. Yoshimoto	365
Structural Analysis of Off-Axis SiC Planes for the Growth of SiC and AlGaN Films K.A. Jones	369
Delineation of Defects Reducing Schottky Barrier Heights on 4H-SiC by the Electrochemical Deposition M. Kato, K. Ogawa and M. Ichimura	373
Investigation of Pits Formed at Oxidation on 4H-SiC Y. Nakano, T. Nakamura, A. Kamisawa and H. Takasu	377
3.3 Point Defects	
Intrinsic Defects in HPSI 6H-SiC: an EPR Study P. Carlsson, N.T. Son, B. Magnusson, A. Henry and E. Janzén	381
Defect Level of the Carbon Vacancy-Carbon Antisite Pair Center in SI 4H SiC M.E. Zvanut, G. Ngetich, H.J. Chung, A.Y. Polyakov, M. Skowronski, N.Y. Garces and E.R. Glaser	385
Behavior of Native Defects in Semi-Insulating 4H-SiC after High Temperature Anneals and Different Cool-Down Rates N.Y. Garces, E.R. Glaser, W.E. Carlos and M.A. Fanton	389
Characterization of Traps in Semi-Insulating 4H-SiC by Discharge Current Transient Spectroscopy M. Takahashi and H. Matsuura	393
The Electronic Structure of the UD-4 Defect in 4H, 6H and 15R SiC A. Gällström, B. Magnusson, A. Thuair, P. PASKOV, A. Henry and E. Janzén	397
Deep Levels Responsible for Semi-Insulating Behavior in Vanadium-Doped 4H-SiC Substrates N.T. Son, P. Carlsson, A. Gällström, B. Magnusson and E. Janzén	401
Contact-Less Electrical Defect Characterization of Semi-Insulating 6H-SiC Bulk Material S. Hahn, F.C. Beyer, A. Gällström, P. Carlsson, A. Henry, B. Magnusson, J.R. Niklas and E. Janzén	405
Photo-EPR Study of Vacancy-Type Defects in Irradiated n-Type 4H-SiC T. Umeda, N. Morishita, T. Ohshima, H. Itoh and J. Isoya	409
New Type of Defects Explored by Theory: Silicon Interstitial Clusters in SiC A. Gali, T. Hornos, N.T. Son and E. Janzén	413

Effect of the Schottky Barrier Height on the Detection of Midgap Levels in 4H-SiC by Deep Level Transient Spectroscopy S.A. Reshanov, G. Pensl, K. Danno, T. Kimoto, S. Hishiki, T. Ohshima, F. Yan, R.P. Devaty and W.J. Choyke	417
Search for Hydrogen Related Defects in p-Type 6H and 4H-SiC G. Alfieri and T. Kimoto	421
Carrier Removal in Electron Irradiated 4H and 6H SiC M. Mikelsen, U. Grossner, J.H. Bleka, E.V. Monakhov, B.G. Svensson, R. Yakimova, A. Henry, E. Janzén and A.A. Lebedev	425
Evolution of D₁-Defect Center in 4H-SiC during High Temperature Annealing S.I. Maximenko, J.A. Freitas, N.Y. Garces, E.R. Glaser and M.A. Fanton	429
The Formation and Annealing of Carbon Interstitial-Related Complexes in Electron-, Proton- and Helium Irradiated 4H SiC J.W. Steeds	433
Identification of Neutral Carbon Vacancy-Carbon Anti-Site Complex by Low Temperature Photoluminescence Spectroscopy J.W. Steeds	437
 3.4 Impurities	
Ionization Energies of Phosphorus Donors in 6H-SiC F. Schmid, K. Semmelroth, M. Krieger, H.B. Weber, G. Pensl and E.E. Haller	441
Wave-Function Symmetry and the Properties of Shallow P Donors in 4H SiC I.G. Ivanov, C. Persson, A. Henry and E. Janzén	445
Infrared PL Signatures of n-Type Bulk SiC Substrates with Nitrogen Impurity Concentration between 10^{16} and 10^{17} cm⁻³ E.R. Glaser, N.Y. Garces, J.D. Caldwell, W.E. Carlos, M.E. Zvanut, B. Magnusson, D.M. Hansen, G.Y. Chung and M.J. Loboda	449
A Comparison of Transient Boron Diffusion in Silicon, Silicon Carbide and Diamond M.K. Linnarsson, J. Isberg, A. Schöner and A. Hallén	453
Diffusion and Electroluminescence Studies of Low Temperature Diffusion of Boron in 3C-SiC I.G. Atabaev, C.C. Tin, B.G. Atabaev, T.M. Saliev, E.N. Bakhranov, N.A. Matchanov, S.L. Lutpullaev, J. Zhang, N.G. Saidkhanova, F.R. Yuzikaeva, I. Nuritdinov, A.K. Islomov, M.Z. Amanov, Rusli and A. Kumta	457
Titanium Related Luminescence in SiC A. Henry, P. Bergman and E. Janzén	461
Raman Investigation of the Effect of Metal Impurities at Gettering Sites on Phonon and Electron Related Properties of 4H-SiC n-n⁺ Junctions M. Kazan, L. Ottaviani and P.M. Masri	465
 3.5 Surface	
Nitrogen Passivation of (0001) 4H-SiC Dangling Bonds G. Pennington and C.R. Ashman	469
Origin of Giant Step Bunching on 4H-SiC (0001) Surfaces Y. Ishida, T. Takahashi, H. Okumura, K. Arai and S. Yoshida	473
 3.6 Fundamental Properties	
Enhanced Annealing of the Main Lifetime Limiting Defect in Thick 4H-SiC Layers L. Storasta, T. Miyazawa and H. Tsuchida	477
Impact of 4H-SiC Substrate Defectivity on Epilayer Injected Carrier Lifetimes R.L. Myers-Ward, K.K. Lew, B.L. VanMil, R.E. Stahlbush, K.X. Liu, J.D. Caldwell, P.B. Klein, P. Wu, M. Fatemi, C.R. Eddy and D.K. Gaskill	481
Generation and Recombination Carrier Lifetimes in 4H SiC Epitaxial Wafers G.Y. Chung, M.J. Loboda, M.J. Marinella, D.K. Schroder, P.B. Klein, T. Isaacs-Smith and J.W. Williams	485
Variations in the Measured Carrier Lifetimes of n⁻ 4H-SiC Epilayers P.B. Klein, J.D. Caldwell, A. Shrivastava and T.S. Sudarshan	489

Investigation of the Internal Carrier Distribution in 4H-SiC Pin-Diodes by Laser Absorption Experiments	
D. Werber, M. Aigner, D. Denoth, F. Wittmann and G. Wachutka	493
Computational Evaluation of Electrical Conductivity on SiC and the Influence of Crystal Defects	
H. Tsuboi, M. Kabasawa, S. Ouchi, M. Sato, R. Sahnoun, M. Koyama, N. Hatakeyama, A. Endou, H. Takaba, M. Kubo, C.A. Del Carpio, Y. Kito, E. Makino, N. Hosokawa, J. Hasegawa, S. Onda and A. Miyamoto	497
Characterization of Electrical Properties in SiC Crystals by Raman Scattering Spectroscopy	
T. Kitamura, S. Nakashima, T. Kato, K. Kojima and H. Okumura	501
Raman Characteristics of Poly 3C-SiC Thin Films Deposited on AlN Buffer Layer	
G.S. Chung and J.H. Jeong	505
Characterization of Electronic Properties of Different SiC Polytypes by All-Optical Means	
K. Neimontas, K. Jarašiūnas, R. Yakimova, M. Syväjärvi and G. Ferro	509
The Specific Features of High-Field Transport in SiC Polytypes	
V.I. Sankin, P.P. Shkrebiy, A.A. Lepneva and M.S. Ramm	513
Thermal Expansion Coefficients of 6H Silicon Carbide	
M. Stockmeier, S.A. Sakwe, P. Hens, P.J. Wellmann, R. Hock and A. Magerl	517
Studies of Thermal Anisotropy in 4H-, 6H-SiC Bulk Single Crystal Wafers by Photopyroelectric (PPE) Method	
P. Wutimakun, H. Miyazaki, Y. Okamoto, J. Morimoto, T. Hayashi and H. Shiomi	521
Improvement of the Thermal Conductivity in 4H-SiC Epitaxial Layer by Introducing Gettering Sites	
L. Ottaviani, M. Kazan, P.M. Masri and T. Sauvage	525
Optical Study of Ge Incorporation in Cubic SiC Layers Grown by VLS	
N. Habka, V. Soulière, J.M. Bluet, M. Soueidan, G. Ferro and B. Nsouli	529
SiC Polytype Stability Influenced by Ge Impurities	
R. Nader, M. Kazan, E. Moussaed, C. Zgheib, B. Nsouli, J. Pezoldt and P.M. Masri	533
Space Charge Waves in 6H-SiC and 4H-SiC	
A.A. Lebedev, M. Lemmer, B. Hilling, M. Wohlecke, M. Imlau, V.V. Bryksin and M. Petrov	537
Galvanomagnetic Properties of 3C-SiC/6H-SiC Heterostructures	
A.A. Lebedev, P.L. Abramov, N.V. Agrinskaya, V.I. Kozub, A.N. Kuznetsov, S.P. Lebedev, G.A. Oganessian, L.M. Sorokin, A.V. Chernyaev and D. Shamshur	541

3.7 Wafer Mapping and Characterization Techniques

Rapid Characterization of SiC Crystals by Full-Wafer Photoluminescence Imaging under Below-Gap Excitation	
H. Isono, M. Tajima, N. Hoshino and H. Sugimoto	545
Mapping of Defects in Large-Area Silicon Carbide Wafers via Photoluminescence and its Correlation with Synchrotron White Beam X-Ray Topography	
Y. Chen, R. Balaji, M. Dudley, M. Murthy, S.I. Maximenko and J.A. Freitas	549
Imaging and Metrology of Silicon Carbide Wafers by Laser-Based Optical Surface Inspection System	
T. Hatakeyama, K. Ichinoseki, N. Higuchi, K. Fukuda and K. Arai	553
Contactless Topographic Analysis of Locally Inhomogeneous Resistivity in SiC and Cd(Zn)Te	
S. Mueller, R. Stibal and W. Jantz	557

Chapter 4: SiC Nanostructures and Graphene

Evolution and Structure of Graphene Layers on SiC(0001)	
C. Riedl, J. Bernardt, K. Heinz and U. Starke	563
Graphene Layers on Silicon Carbide Studied by Raman Spectroscopy	
J. Röhl, M. Hundhausen, K.V. Emtsev, T. Seyller and L. Ley	567
Dots Formation by CVD in the SiC-Si Hetero-System	
M. Bechelany, G. Ferro, J. Dazord, D. Cornu and P. Miele	571
Electronic Band Structure of Cubic Silicon Carbide Nanowires	
A. Miranda, A.E. Ramos and M. Cruz Irissou	575

Theoretical Comparison of 3C-SiC and Si Nanowire FETs in Ballistic Regime K. Rogdakis, M. Bescond, E. Bano and K. Zekentes	579
--	-----

Chapter 5: Processing of SiC

5.1 Milestones

Crystalline Recovery after Activation Annealing of Al Implanted 4H-SiC R. Hattori, T. Watanabe, T. Mitani, H. Sumitani and T. Oomori	585
Dynamical Simulation of SiO₂/4H-SiC Interface on C-Face Oxidation Process: From First Principles T. Ohnuma, A. Miyashita, M. Iwasawa, M. Yoshikawa and H. Tsuchida	591
Influence of the Oxidation Temperature and Atmosphere on the Reliability of Thick Gate Oxides on the 4H-SiC C(000-1) Face M. Grieb, D. Peters, A.J. Bauer, P. Friedrichs and H. Ryssel	597

5.2 Implantation and Doping

Annealing Temperature Dependence of the Electrically Active Profiles and Surface Roughness in Multiple Al Implanted 4H-SiC F. Giannazzo, F. Roccaforte, D. Salinas and V. Raineri	603
Dual-Pearson Approach to Model Ion-Implanted Al Concentration Profiles for High-Precision Design of High-Voltage 4H-SiC Power Devices K. Mochizuki and H. Onose	607
Detection and Characterization of Defects Induced by Ion Implantation/Annealing Process in SiC M. Nagano, H. Tsuchida, T. Suzuki, T. Hatakeyama, J. Senzaki and K. Fukuda	611
Depth Profiling of Al Ion-Implantation Damage in SiC Crystals by Cathodoluminescence Spectroscopy T. Mitani, R. Hattori and M. Yoshikawa	615
Compensation Effects in 7 MeV C Irradiated n-Doped 4H-SiC G. Izzo, G. Litrico, L. Calcagno, G. Foti and F. La Via	619
Structure and Lattice Location of Ge Implanted 4H-SiC T. Kups, K. Tonisch, M. Voelskow, W. Skorupa, A. Konkin and J. Pezoldt	623
Laser Doping of Chromium and Selenium in p-Type 4H-SiC S. Bet, N.R. Quick and A. Kar	627

5.3 Contacts and Etching

Phase Formation and Growth Kinetics of an Interface Layer in Ni/SiC K. Terui, A. Sekiguchi, H. Yoshizaki and J. Koike	631
Backside Nickel Based Ohmic Contacts to n-Type Silicon Carbide R. Ghandi, H.S. Lee, M. Domeij, C. Zetterling and M. Östling	635
Comparison of Electrical Properties of Ohmic Contact Realized on p-Type 4H-SiC D.M. Nguyen, C. Raynaud, M. Lazar, H. Vang and D. Planson	639
Electrical Characteristics of Ti/4H-SiC Slicidation Schottky Barrier Diode A. Kinoshita, T. Nishi, T. Ohyanagi, T. Yatsuo, K. Fukuda, H. Okumura and K. Arai	643
Investigation of Subcontact Layers in SiC after Diffusion Welding O. Korolkov, N. Sleptsuk, A.A. Sitnikova, M. Viljus and T. Rang	647
Isotropic Etching of SiC T. Stauden, F. Niebelschütz, K. Tonisch, V. Cimalla, G. Ecke, C. Haupt and J. Pezoldt	651
4H Silicon Carbide Etching Using Chlorine Trifluoride Gas H. Habuka, Y. Katsumi, Y. Miura, K. Tanaka, Y. Fukai, T. Fukae, Y. Gao, T. Kato, H. Okumura and K. Arai	655
Anisotropic Etching of SiC in the Mixed Gas of Chlorine and Oxygen T. Hatayama, T. Shimizu, H. Yano, Y. Uraoka and T. Fuyuki	659

5.4 Oxides and Other Dielectrics

Model Calculation of SiC Oxidation Rates in the Thin Oxide Regime Y. Hijikata, T. Yamamoto, H. Yaguchi and S. Yoshida	663
Oxygen-Partial-Pressure Dependence of SiC Oxidation Rate Studied by <i>In Situ</i> Spectroscopic Ellipsometry T. Yamamoto, Y. Hijikata, H. Yaguchi and S. Yoshida	667
TEM Observation of SiO₂/4H-SiC Hetero Interface H. Matsuhata, J. Senzaki, I. Nagai and H. Yamaguchi	671
Influence of Metallization Annealing on Channel Mobility in 4H-SiC MOSFET on Carbon Face S. Harada, M. Kato, T. Yatsuo, K. Fukuda and K. Arai	675
Enhanced Channel Mobility in 4H-SiC MISFETs by Utilizing Deposited SiN/SiO₂ Stack Gate Structures M. Noborio, J. Suda and T. Kimoto	679
Anomalous High Channel Mobility in SiC-MOSFETs with Al₂O₃/SiO_x/SiC Gate Structure S. Hino, T. Hatayama, J. Kato, N. Miura, T. Oomori and E. Tokumitsu	683
Scattering Mechanisms in Silicon Carbide MOSFETs with Gate Oxides Fabricated Using Sodium Enhanced Oxidation Technique V. Tilak, K. Matocha, G. Dunne, F. Allerstam and E.Ö. Sveinbjörnsson	687
High Channel Mobility of MOSFET Fabricated on 4H-SiC (11-20) Face Using Wet Annealing T. Endo, E. Okuno, T. Sakakibara and S. Onda	691
High Channel Mobility of 4H-SiC MOSFET Fabricated on Macro-Stepped Surface T. Masuda, S. Harada, T. Tsuno, Y. Namikawa and T. Kimoto	695
Improvement of Electron Channel Mobility in 4H SiC MOSFET by Using Nitrogen Implantation F. Moscatelli, R. Nipoti, S. Solmi, S. Cristiani, M. Sanmartin and A. Poggi	699
Reduction of Interface Traps and Enhancement of Channel Mobility in n-Channel 6H-SiC MOSFETs by Irradiation with Gamma-Rays S. Hishiki, S.A. Reshanov, T. Ohshima, H. Itoh and G. Pensl	703
Effects of Fabrication Process on the Electrical Characteristics of n-Channel MOSFETs Irradiated with Gamma-Rays S. Hishiki, N. Iwamoto, T. Ohshima, H. Itoh, K. Kojima and K. Kawano	707
4H-SiC p-Channel MOSFETs with Epi-Channel Structure M. Okamoto, T. Yatsuo, K. Fukuda, H. Okumura and K. Arai	711
Atomistic Scale Modeling of Factors Affecting the Channel Mobility in 4H-SiC MOSFETs A. Chatterjee, A. Bhat and K. Matocha	715
Electrically Detected Magnetic Resonance Studies of Processing Variations in 4H SiC Based MOSFETs C.J. Cochrane, P.M. Lenahan and A.J. Lelis	719
The Inefficiency of H₂-Passivation as a Criterion for the Origin of SiC/SiO₂ Deep Interface States - a Theoretical Study J.M. Knaup, P. Deák and T. Frauenheim	723
Two Different Species of Traps Monitored at N-Implanted 3C-SiC MOS Capacitors by Conductance Spectroscopy S. Beljakowa, M. Krieger, T. Frank, G. Pensl, L. Trapaidze, N. Hatta, M. Abe, H. Nagasawa and A. Schöner	727
Effect of Post-Oxidation Annealing on High-Temperature Grown SiO₂/4H-SiC Interface J.H. Moon, K.Y. Cheong, H.K. Song, J.H. Yim, M.S. Oh, J.H. Lee, W. Bahng, N.K. Kim and H.J. Kim	731
Influence of Ambient, Gate Metal and Oxide Thickness on Interface State Density and Time Constant in MOSiC Capacitor S. Nakagomi, K. Sato, S. Suzuki and Y. Kokubun	735
High Frequency Inversion Capacitance Measurements for 6H-SiC n-MOS Capacitors from 450 to 600 °C R.N. Ghosh, R. Loloee, T. Isaacs-Smith and J.R. Williams	739
The Effect of Nitridation on SiC MOS Oxides as Evaluated by Charge Pumping D.B. Habersat, A.J. Lelis, J.M. McGarrity, F.B. McLean and S. Potbhare	743
Criteria for Accurate Measurement of Charge-Pumping Current in 4H-SiC MOSFETs D. Okamoto, H. Yano, T. Hatayama, Y. Uraoka and T. Fuyuki	747

Optimization of 4H-SiC MOS Properties with Cesium Implantation Y. Wang, T. Khan and T.P. Chow	751
A Study of Deep Energy-Level Traps at the 4H-SiC/SiO₂ Interface and Their Passivation by Hydrogen F. Allerstam and E.Ö. Sveinbjörnsson	755
Interface and Carrier Transport Behaviour in Al/HfO₂/SiO₂/SiC Structure R. Mahapatra, A.B. Horsfall and N.G. Wright	759
Improved Properties of AlON/4H SiC Interface for Passivation Studies M. Wolborski, D.M. Martin, M. Bakowski, A. Hallén and I. Katardjiev	763
Influence of Annealing on the Al₂O₃/4H-SiC Interface U. Grossner, M. Avice, S. Diplas, A. Thøgersen, J.S. Christensen, B.G. Svensson, O. Nilsen, H. Fjellvåg and J.F. Watts	767
Post Metallization Annealing Characterization of Interface Properties of High-κ Dielectrics Stack on Silicon Carbide M.H. Weng, R. Mahapatra, N.G. Wright and A.B. Horsfall	771
Correlation between Thermal Oxide Breakdown and Defects in n-Type 4H-SiC Epitaxial Wafers S.I. Soloviev, K. Matocha, G. Dunne and Z. Stum	775
Reliability of Thermal Oxides Grown on n-Type 4H-SiC Implanted with Low Nitrogen Concentration J. Senzaki, A. Shimozato, K. Fukuda and K. Arai	779
Impact of the Wafer Quality on the Reliability of MOS Structure on the C-Face of 4H-SiC T. Hatakeyama, T. Suzuki, J. Senzaki, K. Fukuda, H. Matsuhata, T. Shinohe and K. Arai	783
Gate-Area Dependence of SiC Thermal Oxides Reliability J. Senzaki, A. Shimozato, M. Okamoto, K. Kojima, K. Fukuda, H. Okumura and K. Arai	787
Effect of Gate Wet Reoxidation on Reliability and Channel Mobility of Metal-Oxide-Semiconductor Field-Effect Transistors Fabricated on 4H-SiC(000-1) T. Suzuki, J. Senzaki, T. Hatakeyama, K. Fukuda, T. Shinohe and K. Arai	791
Negative Field Reliability of ONO Gate Dielectric on 4H-SiC S. Tanimoto, T. Suzuki, S. Yamagami, H. Tanaka, T. Hayashi, Y. Hirose and M. Hoshi	795
TDDDB Measurement of Gate SiO₂ on 4H-SiC Formed by Chemical Vapor Deposition K. Fujihira, S. Yoshida, N. Miura, Y. Nakao, M. Imaizumi, T. Takami and T. Oomori	799
Impact of Nitridation on Negative and Positive Charge Buildup in SiC Gate Oxides J. Rozen, S. Dhar, S.W. Wang, V.V. Afanas'ev, S.T. Pantelides, J.R. Williams and L.C. Feldman	803
Temperature-Dependence of SiC MOSFET Threshold-Voltage Instability A.J. Leis, D.B. Habersat, R. Green and N. Goldsman	807
Characteristics of Sol-Gel Derived SiO₂ Thick Film on 4H-SiC J.L. Tan, K.Y. Cheong and Rusli	811

5.5 Polishing and Related Processes

New Chemical Planarization of SiC and GaN Using an Fe Plate in H₂O₂ Solution J. Murata, A. Kubota, K. Yagi, Y. Sano, H. Hara, K. Arima, T. Okamoto, H. Mimura and K. Yamauchi	815
Development of Lapping and Polishing Technologies of 4H-SiC Wafers for Power Device Applications H. Yashiro, T. Fujimoto, N. Ohtani, T. Hoshino, M. Katsuno, T. Aigo, H. Tsuge, M. Nakabayashi, H. Hirano and K. Tatsumi	819
Improvements in Electrical Properties of SiC Surface Using Mechano-Chemical Polishing K. Hotta, K. Hirose, Y. Tanaka, K. Kawata and O. Eryu	823
The Impact of Chemical-Mechanical Polishing on Defective 4H-SiC Schottky Barrier Diodes K.Y. Lee, W.Z. Chen and M.A. Capano	827
Effect of Process Parameters on Material Removal Rate in Chemical Mechanical Polishing of 6H-SiC(0001) J.H. An, G.S. Lee, W.J. Lee, B.C. Shin, J.D. Seo, K.R. Ku, H.D. Seo and H.D. Jeong	831
Damage-Free Planarization of 2-Inch 4H-SiC Wafer Using Pt Catalyst Plate and HF Solution T. Okamoto, Y. Sano, H. Hara, K. Arima, K. Yagi, J. Murata, H. Mimura and K. Yamauchi	835

The Preparation of World-Class Single Crystal Silicon Carbide Wafers Using High Rate Chemical Mechanical Planarization Slurries	
M.L. White, S. Reggie, N. Naguib, K. Nicholson, J. Gilliland and A. Walters	839
Beveling of Silicon Carbide Wafer by Plasma Chemical Vaporization Machining	
T. Kato, Y. Sano, H. Hara, H. Mimura, K. Yamamura and K. Yamauchi	843
Temperature Dependence of Plasma Chemical Vaporization Machining of Silicon and Silicon Carbide	
Y. Sano, M. Watanabe, T. Kato, K. Yamamura, H. Mimura and K. Yamauchi	847
Electric Discharge Machining for Silicon Carbide and Related Materials	
S. Yamaguchi, T. Noro, H. Takahashi, H. Majima, Y. Nagao, K. Ishikawa, Y. Zhou and T. Kato	851
Characterization of Electric Discharge Machining for Silicon Carbide Single Crystal	
T. Kato, T. Noro, H. Takahashi, S. Yamaguchi and K. Arai	855

5.6 Micromachining and MEMS

A Silicon Carbide Accelerometer for Extreme Environment Applications	
S. Rajgopal, D. Zula, S. Garverick and M. Mehregany	859
An Examination of Material-Related Performance in SiC Heated Elements for IR Emitter and Sensor Applications	
L. Chen and M. Mehregany	863
Mechanical Properties of Poly 3C-SiC Thin Films According to Carrier Gas (H₂) Concentration	
G.S. Chung and K.B. Han	867
Novel Use of Columnar Porous Silicon Carbide Structures as Nanoimprint Lithography Stamps	
J.H. Leach, H. Morkoç, Y. Ke, R.P. Devaty and W.J. Choyke	871
Etching Characteristics of Polycrystalline 3C-SiC Films Using Enhanced RIE	
G.S. Chung and C.M. Ohn	875
Femtosecond Laser-Induced Surface Patterning on 4H-SiC	
T. Tomita, R. Kumai, K. Kinoshita, S. Matsuo, S. Hashimoto, H. Nagase, M. Nakajima and T. Suemoto	879
Cross-Sectional TEM Analysis of Structural Change in 4H-SiC Single Crystal Irradiated by Femtosecond Laser Pulses	
H. Kawahara, T. Okada, R. Kumai, T. Tomita, S. Matsuo, S. Hashimoto and M. Yamaguchi	883

Chapter 6: SiC Devices

6.1 Milestones

Present Status and Future Prospects for Electronics in EVs/HEVs and Expectations for Wide Bandgap Semiconductor Devices	
K. Hamada	889
Critical Technical Issues in High Voltage SiC Power Devices	
A.K. Agarwal, A.A. Burk, R. Callanan, C. Capell, M.K. Das, S.K. Haney, B.A. Hull, C. Jonas, M.J. O'Loughlin, M. O'Neil, J.W. Palmour, A.R. Powell, J. Richmond, S.H. Ryu, R.E. Stahlbush, J.J. Sumakeris and Q.J. Zhang	895
SiC JFET: Currently the Best Solution for an Unipolar SiC High Power Switch	
K. Rueschenschmidt, M. Treu, R. Rupp, P. Friedrichs, R. Elpelt, D. Peters and P. Blaschitz	901
Challenges of 4H-SiC MOSFETs on the C(000-1) Face toward the Achievement of Ultra Low On-Resistance	
K. Fukuda, S. Harada, J. Senzaki, M. Okamoto, Y. Tanaka, A. Kinoshita, R. Kosugi, K. Kojima, M. Kato, A. Shimozato, K. Suzuki, Y. Hayashi, K. Takao, T. Kato, S.I. Nishizawa, T. Yatsuo, H. Okumura, H. Ohashi and K. Arai	907
Normally-Off 1400V/30A 4H-SiC DACFET and its Application to DC-DC Converter	
M. Kitabatake, M. Tagome, S. Kazama, K. Yamashita, K. Hashimoto, K. Takahashi, O. Kusumoto, K. Utsunomiya, M. Hayashi, M. Uchida, R. Ikegami, C. Kudo and S. Hashimoto	913
Applications-Based Design of SiC Technology	
N.G. Wright, C.M. Johnson, A.B. Horsfall, C. Buttay, K. Vassilevski, W.S. Loh, R. Skuriat and P. Agyakwa	919

New Applications in Power Electronics Based on SiC Power Devices H. Morel, D. Bergogne, D. Planson, B. Allard and R. Meuret	925
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6.2 Schottky Barrier Diodes

Development of Large Area (up to 1.5 cm²) 4H-SiC 10 kV Junction Barrier Schottky Rectifiers B.A. Hull, J.J. Sumakeris, M.J. O'Loughlin, Q.J. Zhang, J. Richmond, A.R. Powell, M.J. Paisley, V.F. Tsvetkov, A. Hefner and A. Rivera	931
Reliability Aspects of High Voltage 4H-SiC JBS Diodes P. Brosselard, N. Camara, X. Jordá, M. Vellvehi, E. Bano, J. Millan and P. Godignon	935
1200-V JBS Diodes with Low Threshold Voltage and Low Leakage Current T. Yamamoto, J. Kojima, T. Endo, E. Okuno, T. Sakakibara and S. Onda	939
High-Current 10 kV SiC JBS Rectifier Performance E.A. Imhoff and K.D. Hobart	943
5 kV, 9.5 A SiC JBS Diodes with Non-Uniform Guard Ring Edge Termination for High Power Switching Application J. Hu, L.X. Li, P. Alexandrov, X.H. Wang and J.H. Zhao	947
10 kV Silicon Carbide Junction Barrier Schottky Rectifier T. McNutt, S. Van Campen, A. Walker, K. Ha, C. Kirby, M. Sherwin, R. Singh and H. Hearne	951
Breakdown Behavior of 900-V 4H-SiC Schottky Barrier Diodes Terminated with Boron-Implanted pn-Junction P.A. Ivanov and I.V. Grekhov	955
Effect of the Doping Concentration and Space of Both p-Grid and Field Limiting Ring on 4H-SiC Junction Barrier Schottky Diode with Single Ion Implantation Process I.H. Kang, J.Y. Song, S.J. Joo, W. Bahng, S.C. Kim and N.K. Kim	959
Structure Analysis of In-Grown Stacking Faults and Investigation of the Cause for High Reverse Current of 4H-SiC Schottky Barrier Diode S. Harada, Y. Namikawa and R. Sugie	963
Characterization of Schottky Diodes on 4H-SiC with Various Off-Axis Angles Grown by Sublimation Epitaxy M. Nakamura, Y. Hashino, T. Furusho, H. Kinoshita, H. Shiomi and M. Yoshimoto	967
Schottky Barrier Diode Fabricated by MOCVD-Grown Epilayer Using Bis-Trimethylsilylmethane Precursor H.K. Song, J.H. Lee, M.S. Oh, J.H. Moon, H.S. Seo, J.H. Yim, S.Y. Kwon and H.J. Kim	971
Device Simulation Model for Transient Analysis of SiC-SBD M. Tomita, Y. Maeyama, M. Sato, Y. Fukuda, F. Honma, J. Ono, M. Shimizu and H. Iwakuro	975
Distribution of Forward Voltage of SiC Schottky Barrier Diode Using Ti Sintering Process K. Kuroda, Y. Matsuno, K. Ohtsuka, N. Yutani, S. Shikama and H. Sumitani	979
Impact of High-k Dielectrics on Breakdown Performances of SiC and Diamond Schottky Diodes G. Brezeanu, M. Brezeanu, C. Boianceanu, F. Udrea, G.A.J. Amaratunga and P. Godignon	983
Field-Plate Terminated Pt/n- 4H-SiC SBD Using Thermal SiO₂ and Sputter Deposited AlN Dielectric Stack A. Kumta, E. Rusli and J.H. Xia	987

6.3 PiN Diodes

3.3 kV-10A 4H-SiC PiN Diodes P. Brosselard, N. Camara, J. ul Hassan, X. Jordá, P. Bergman, J. Montserrat and J. Millan	991
Bevel Mesa Combined with Implanted Junction Termination Structure for 10 kV SiC PiN Diodes T. Hiyoshi, T. Hori, J. Suda and T. Kimoto	995
Observation of Crystalline Defects Causing pn Junction Reverse Leakage Current T. Watanabe, Y. Nakao, K. Fujihira, N. Miura, Y. Tarui, M. Imaizumi and T. Oomori	999
Comparative Evaluation of Anode Layers on the Electrical Characteristics of High Voltage 4H-SiC PiN Diodes P.A. Losee, Y. Wang, C.H. Li, S.K. Sharma, I. Bhat, T.P. Chow and R.J. Gutmann	1003
Self-Heating of 4H-SiC PiN Diodes at High Current Densities M.E. Levinshtein, T.T. Mnatsakanov, P.A. Ivanov, J.W. Palmour, M.K. Das and B.A. Hull	1007

Impact of RIE Etching on the Breakdown Voltage of 4H-SiC Mesa Diodes H. Vang, S. Scharnholtz, C. Raynaud, M. Lazar, G. Pâques and D. Planson	1011
Novel SiC Zener Diodes with High Operating Temperature of 300°C and High Power Density of 40 kW/cm² R. Ishii, K. Nakayama, H. Tsuchida and Y. Sugawara	1015
Microwave Switches and Modulators Based on 4H-SiC p-i-n Diodes K. Zekentes, V.V. Basanets, M.S. Boltovets, V.A. Kryvutsa, V.O. Orechovskij, V.I. Simonchuk, A.V. Zorenko, L.P. Romanov, A.V. Kirillov, E. Bano and N. Camara	1019
Annealing Effect on Characteristics of p⁺n 4H-SiC Diode Formed by Al Ion Implantation M. Satoh, S. Miyagawa, T. Kudoh, A. Egami, K. Numajiri and M. Shibagaki	1023
Room Temperature Annealing Effects on Leakage Current of Ion Implanted p⁺n 4H-SiC Diodes F. Moscatelli, F. Bergamini, A. Poggi, M. Passini, F. Tamarri, M. Bianconi and R. Nipoti	1027
Determination of Ambipolar Lifetime and Epilayer Thickness of 5kV SiC Bipolar Devices by Transient Switching Studies T. Ben Salah, S. Risaletto, C. Raynaud, K. Besbes, D. Bergogne, D. Planson and H. Morel	1031
Numerical Evaluation of Forward Voltage in SiC Pin Diode with Non-Ohmic Current Component in Contact to p-Type Layer K. Ohtsuka, Y. Tarui, T. Watanabe, K. Fujihira and Y. Matsuno	1035
Transient Response to High Energy Heavy Ions in 6H-SiC n⁺p Diodes S. Onoda, T. Ohshima, T. Hirao, S. Hishiki, N. Iwamoto, K. Kojima and K. Kawano	1039
Degradation of Charge Collection Efficiency for 6H-SiC Diodes by Electron Irradiation N. Iwamoto, S. Onoda, S. Hishiki, T. Ohshima, M. Murakami, I. Nakano and K. Kawano	1043

6.4 JFETs and MESFETs

1200-V, 50-A, Silicon Carbide Vertical Junction Field Effect Transistors for Power Switching Applications V. Veliadis, T. McNutt, M. McCoy, H. Hearne, G. De Salvo, C. Clarke, P. Potyraj and C. Scozzie	1047
High-Temperature Static and Dynamic Reliability Study of 4H-SiC Vertical-Channel JFETs for High-Power System Applications L. Cheng, P. Martin, M.S. Mazzola, D.C. Sheridan, R.L. Kelly, V. Bondarenko, S. Morrison, R. Gray, G. Tian, J.D. Scofield, J.R.B. Casady and J.B. Casady	1051
High-Temperature Operation of 50 A (1600 A/cm²), 600 V 4H-SiC Vertical-Channel JFETs for High-Power Applications L. Cheng, I. Sankin, V. Bondarenko, M.S. Mazzola, J.D. Scofield, D.C. Sheridan, P. Martin, J.R.B. Casady and J.B. Casady	1055
Normally-Off 4H-SiC Vertical JFET with Large Current Density H. Shimizu, Y. Onose, T. Someya, H. Onose and N. Yokoyama	1059
Silicon Carbide Vertical JFET Operating at High Temperature K. Vassilevski, K.P. Hilton, N.G. Wright, M.J. Uren, A.G. Munday, I.P. Nikitina, A.J. Hydes, A.B. Horsfall and C.M. Johnson	1063
Switching Performance of Epitaxially Grown Normally-Off 4H-SiC JFET R.K. Malhan, S.J. Rashid, M. Kataoka, Y. Takeuchi, N. Sugiyama, F. Udrea, G.A.J. Amaratunga and T. Reimann	1067
1270V, 1.21mΩ·cm² SiC Buried Gate Static Induction Transistors (SiC-BGSITs) Y. Tanaka, K. Yano, M. Okamoto, A. Takatsuka, K. Arai and T. Yatsuo	1071
Three Dimensional Analysis of Turnoff Operation of SiC Buried Gate Static Induction Transistors (BG-SITs) K. Yano, Y. Tanaka, T. Yatsuo, A. Takatsuka, M. Okamoto and K. Arai	1075
Fabrication and Testing of 6H-SiC JFETs for Prolonged 500 °C Operation in Air Ambient D.J. Spry, P.G. Neudeck, L.Y. Chen, G.M. Beheim, R.S. Okojie, C.W. Chang, R.D. Meredith, T.L. Ferrier and L.J. Evans	1079
Silicon Carbide Differential Amplifiers for High-Temperature Sensing A. Patil, X.A. Fu, P.G. Neudeck, G.M. Beheim, M. Mehregany and S. Garverick	1083
SiC Lateral Trench JFET for Harsh-Environment Wireless Systems I. Sankin, V. Bondarenko, D.C. Sheridan, M.S. Mazzola, J.B. Casady, J. Fraley and M. Schupbach	1087
Development of High Temperature Lateral HV and LV JFETs in 4H-SiC Y. Zhang, K. Sheng, M. Su, J.H. Zhao, P. Alexandrov and L. Fursin	1091

Fast Switching Characteristics of 4H-SiC RESURF-Type JFET K. Fujikawa, K. Sawada, T. Tsuno, H. Tamaso, S. Harada and Y. Namikawa	1095
6H-SiC Lateral JFETs for Analog Integrated Circuits X.A. Fu, A. Patil, P.G. Neudeck, G.M. Beheim, S. Garverick and M. Mehregany	1099
Influence of Passivation Oxide Properties on SiC Field-Plated Buried Gate MESFETs P.Å. Nilsson, M. Sudow, F. Allerstam, K. Andersson, E.Ö. Sveinbjörnsson, H. Hjelmgren and N. Rorsman	1103
RF Characteristics of a Fully Ion-Implanted MESFET with Highly Doped Thin Channel Layer on a Bulk Semi-Insulating 4H-SiC Substrate. S. Katakami, S. Ono and M. Arai	1107
Measurement of Local Temperatures Using μ-Raman of SiC and AlGaIn-GaN/SiC Power and RF Devices O.J. Glembocki, J.D. Caldwell, J.A. Mittereder, J.P. Calame, S.C. Binari and R.E. Stahlbush	1111

6.5 MOSFETs

Normally-Off 4H-SiC Power MOSFET with Submicron Gate K. Yamashita, K. Egashira, K. Hashimoto, K. Takahashi, O. Kusumoto, K. Utsunomiya, M. Hayashi, M. Uchida, C. Kudo, M. Kitabatake and S. Hashimoto	1115
(11-20) Face Channel MOSFET with Low On-Resistance E. Okuno, T. Endo, J. Kawai, T. Sakakibara and S. Onda	1119
Investigation into Short-Circuit Ruggedness of 1.2 kV 4H-SiC MOSFETs Y. Nakao, S. Watanabe, N. Miura, M. Imaizumi and T. Oomori	1123
Effect of Recombination-Induced Stacking Faults on Majority Carrier Conduction and Reverse Leakage Current on 10 kV SiC DMOSFETs S.H. Ryu, F. Husna, S.K. Haney, Q.C.J. Zhang, R.E. Stahlbush and A.K. Agarwal	1127
950 Volt 4H-SiC MOSFETs: DC and Transient Performance and Gate Oxide Reliability K. Matocha, Z. Stum, S. Arthur, G. Dunne and L. Stevanovic	1131
Evaluation of 4H-SiC DMOSFETs for High-Power Electronics Applications R. Green, A. Ogunniyi, D. Ibitayo, G. Koebke, M. Morgenstern, A.J. Lelis, C. Dickens and B.A. Hull	1135
Comparison of 10 kV 4H-SiC Power MOSFETs and IGBTs for High Frequency Power Conversion G.G. Walden, T. McNutt, M. Sherwin, S. Van Campen, R. Singh and R. Howell	1139
On-State and Switching Performance of High-Voltage 15 – 20 kV 4H-SiC DMOSFETs and IGBTs T. Tamaki, G.G. Walden, Y. Sui and J.A. Cooper	1143
Temperature and Time Dependent Threshold Voltage Instability in 4H-SiC Power DMOSFET Devices M.J. Tadjer, K.D. Hobart, E.A. Imhoff and F.J. Kub	1147

6.6 Bipolar Transistors and Thyristors

1200 V 4H-SiC BJTs with a Common Emitter Current Gain of 60 and Low On-Resistance H.S. Lee, M. Domeij, C. Zetterling, R. Ghandi, M. Östling, F. Allerstam and E.Ö. Sveinbjörnsson	1151
1600 V, 5.1 mΩ•cm² 4H-SiC BJT with a High Current Gain of $\beta=70$ J.H. Zhang, P. Alexandrov and J.H. Zhao	1155
4H-SiC Bipolar Junction Transistors with a Current Gain of 108 Q.J. Zhang, C. Jonas, A.A. Burk, C. Capell, J. Young, R. Callanan, A.K. Agarwal, J.W. Palmour, B. Geil and C. Scozzie	1159
Simulation and Modeling of Thermal Effects in 4H-SiC NPN BJTs C.F. Huang and C.Y. Tseng	1163
Reliability Testing of 4H-SiC Bipolar Junction Transistors in Continuous Switching Applications S.L. Kaplan and A. Ogunniyi	1167
A Simple and Reliable Electrical Method for Measuring the Junction Temperature and Thermal Resistance of 4H-SiC Power Bipolar Junction Transistors K.G.P. Eriksson, M. Domeij, H.S. Lee, C. Zetterling and M. Östling	1171
Behavior of Stacking Faults in TEDREC Phenomena for 4.5 kV SiCGT K. Nakayama, Y. Sugawara, Y. Miyanagi, K. Asano, S. Ogata, S. Okada, T. Izumi and A. Tanaka	1175

Electron Irradiation Lifetime Control for SiC Bipolar Devices of 200 kVA High Power SiC Inverters	
Y. Sugawara, S. Ogata, Y. Miyanagi, K. Asano, S. Okada, A. Tanaka, K. Nakayama and T. Izumi	1179
A 13 kV 4H-SiC n-Channel IGBT with Low $R_{diff,on}$ and Fast Switching	
M.K. Das, Q.J. Zhang, R. Callanan, C. Capell, J. Clayton, M. Donofrio, S.K. Haney, F. Husna, C. Jonas, J. Richmond and J.J. Sumakeris	1183
12 kV 4H-SiC p-IGBTs with Record Low Specific On-Resistance	
Q.J. Zhang, C. Jonas, J.J. Sumakeris, A.K. Agarwal and J.W. Palmour	1187
Design, Simulation, and Characterization of High-Voltage SiC p-IGBTs	
Y. Sui, J.A. Cooper, X. Wang and G.G. Walden	1191
SiC Based Optically-Gated High-Power Solid-State Switch for Pulsed-Power Application	
S.K. Mazumder and T. Sarkar	1195

6.7 Sensors and Detectors

Hydrogen Gas Sensors Fabricated on Atomically Flat 4H-SiC Webbed Cantilevers	
P.G. Neudeck, D.J. Spry, A.J. Trunek, L.J. Evans, L.Y. Chen, G.W. Hunter and D. Androjna	1199
4H-SiC Single Photon Avalanche Diode for 280nm UV Applications	
J. Hu, X.B. Xin, P. Alexandrov, J.H. Zhao, B.L. VanMil, D.K. Gaskill, K.K. Lew, R.L. Myers-Ward and C.R. Eddy	1203
Avalanche Multiplication and Impact Ionisation in Separate Absorption and Multiplication 4H-SiC Avalanche Photodiodes	
W.S. Loh, J. David, S.I. Soloviev, H.Y. Cha, P.M. Sandvik, J.S. Ng and C.M. Johnson	1207
Observation of Luminescence from Defects in 4H-SiC APDs Operating in Avalanche Breakdown	
S.I. Soloviev, P.M. Sandvik, A. Vertiatchikh, K. Dovidenko and H.Y. Cha	1211
Schottky Barrier Lowering in 4H-SiC Schottky UV Detector	
A. Sciuto, F. Roccaforte, S. Di Franco and V. Raineri	1215
The Influence of Radiation Defects on the Charge Transport in SiC Nuclear Detectors in Conditions of Elevated Temperatures and Deep Compensation of the Conductivity	
A.M. Ivanov, N.B. Strokan, A.A. Lebedev and V.V. Kozlovski	1219

6.8 Packaging, Circuits, and System Applications

High Power-Density SiC Converter	
S.I. Kinouchi, H. Nakatake, T. Kitamura, S. Azuma, S. Tominaga, S. Nakata, Y. Nakao, T. Oi and T. Oomori	1223
3D Thermal Stress Model for SiC Power Modules	
B.H. Tsao, J. Lawson, J.D. Scofield, C. Laing and J. Brown	1227
Efficiency Improvement of PV-Inverters with SiC-DMOSFETs	
B. Burger, D. Kranzer and O. Stalter	1231
A High Performance CCM PFC Circuit Using a SiC Schottky Diode and a Si SuperFET™ Switch	
W.S. Choi, S.M. Young, R.L. Woodin, A.W. Witt and J. Shovlin	1235
Summary of SiC Research for Transportation Applications at ORNL	1239

Chapter 7: III-Nitrides and Other Related Materials

7.1 Milestones

LPE Growth of Bulk GaN Crystal by Alkali-Metal Flux Method	
F. Kawamura, H. Umeda, M. Morishita, R. Gejo, M. Tanpo, M. Imade, N. Miyoshi, M. Yoshimura, Y. Mori, T. Sasaki and Y. Kitaoka	1245
600V GaN Schottky Barrier Power Devices for High Volume and Low Cost Applications	
L.L. Liu, T.G. Zhu, M. Murphy, M. Pabisz, M. Pophristic, B. Peres and T. Hierl	1251
Status of GaN-Based Power Switching Devices	
M. Hikita, H. Ueno, H. Matsuo, T. Ueda, Y. Uemoto, K. Inoue, T. Tanaka and D. Ueda	1257
Progress in GaN MOSFET Technology	
T.P. Chow, W. Huang, T. Khan, K. Matocha and Y. Wang	1263

7.2 Growth of III-Nitrides

Growth of Thick AlN Layers by High Temperature CVD (HTCVD)

A. Claudel, E. Blanquet, D. Chaussende, M. Audier, D. Pique and M. Pons 1269

Epitaxial Lateral Overgrowth of (1-100) m-Plane GaN on m-Plane 6H-SiC by Metalorganic Chemical Vapor Deposition

X. Ni, Ü. Özgür, S. Chevtchenko, J. Nie, H. Morkoç, R.P. Devaty and W.J. Choyke 1273

Growth and Characterization of AlGaIn/GaN HEMT Structures on 3C-SiC/Si(111) Templates

Y. Cordier, M. Portail, S. Chenot, O. Tottereau, M. Zielinski and T. Chassagne 1277

Semipolar Nitrides Grown on Si(001) Offcut Substrates with 3C-SiC Buffer Layers

Y. Abe, J. Komiyama, T. Isshiki, S. Suzuki, A. Yoshida, H. Ohishi and H. Nakanishi 1281

Surface Morphology of AlN Epitaxial Layer Grown on Various SiC Substrates by Sublimation Closed Space Technique

G.S. Lee, M.O. Kyun, H.H. Hwang, J.H. An, W.J. Lee, B.C. Shin and S. Nishino 1285

Effects of 3C-SiC Intermediate Layer on the Properties of AlN Films Grown on SiO₂/Si Substrate

G.S. Chung and T.W. Lee 1289

7.3 Physical Properties and Characterization of III-Nitrides

Raman Scattering Analysis of Electrical Property and Crystallinity in Freestanding GaN Crystals with Various Impurity Concentrations

T. Kitamura, S. Nakashima and H. Okumura 1293

Characterization of Traps in GaN pn Junctions Grown by MOCVD on GaN Substrate Using Deep-Level Transient Spectroscopy

Y. Tokuda, Y. Matsuoka, H. Ueda, O. Ishiguro, N. Soejima and T. Kachi 1297

Optical Characterization of Defect-Related Carrier Recombination and Transport Features in GaN Substrates and CVD Diamonds

K. Jarašiūnas, T. Malinauskas, R. Aleksiejunas, B. Monemar, V. Ralchenko, A. Gontar and E. Ivakin 1301

Characterization of V-Defects in InGaIn Single-Quantum-Well Films at Nanometer Level by High Spatial Resolution Cathodoluminescence Spectroscopy

M. Yoshikawa, M. Murakami, T. Fujita, K. Inoue, K. Matsuda, H. Ishida and H. Harima 1305

Correlation between Screw Dislocations Distribution and Cathodoluminescence Spectra of InGaIn Single Quantum Well Films

T. Fujita, T. Mitani, M. Murakami, M. Yoshikawa and H. Harima 1309

Material Properties of GaN Films Grown on SiC/SOI Substrate

Z.C. Feng, C. Tran, I.T. Ferguson and J.H. Zhao 1313

HRTEM Analysis of AlN Layer Grown on 3C-SiC/Si Heteroepitaxial Substrates with Various Surface Orientations

T. Isshiki, K. Nishio, Y. Abe, J. Komiyama, S. Suzuki and H. Nakanishi 1317

7.4 III-Nitride Devices

288 V-10 V DC-DC Converter Application Using AlGaIn/GaN HFETs

S. Yoshida, M. Masuda, Y. Niiyama, J. Li, N. Ikeda and T. Nomura 1321

Multiple Ion-Implanted GaN/AlGaIn/GaN HEMTs with Remarkably Low Parasitic Source Resistance

K. Nomoto, M. Satoh and T. Nakamura 1325

Current Collapse in AlGaIn/GaN/AlGaIn Double Heterojunction Field Effect Transistors

M. Shimizu, M. Inada, S. Yagi, A. Nakajima, H. Okumura, A. Ubukata, Y. Yano and N. Akutsu 1329

Current Collapse Characteristic of AlGaIn/GaN MIS-HEMT

S. Yagi, M. Shimizu, Y. Yano, A. Ubukata and N. Akutsu 1333

The Effect of Ohmic Contact Location on the Buffer Leakage Current of AlGaIn/GaN Heterostructure

Y.H. Choi, J.Y. Lim, K.H. Cho, I.H. Ji and M.K. Han 1337

Electrical Properties of Inhomogeneous Pt/GaN Schottky Barrier

F. Roccaforte, F. Iucolano, F. Giannazzo, S. Di Franco, V. Puglisi and V. Raineri 1341

Effect of Deep Trap on Breakdown Voltage in AlGa_N/Ga_N HEMTs A. Nakajima, S. Yagi, M. Shimizu and H. Okumura	1345
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7.5 Other Related Materials

DC and RF Performance of Diamond MISFETs with Alumina Gate Insulator K. Hirama, Y. Jingu, M. Ichikawa, H. Umezawa and H. Kwarada	1349
--	------

Diamond Doped by Hot Ion Implantation N. Tsubouchi, M. Ogura, H. Watanabe, A. Chayahara and H. Okushi	1353
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Characterization of Nanometer-Sized ZnO by Raman and Cathodoluminescence Spectroscopies K. Inoue, T. Nakagawa, M. Yoshikawa, N. Hasuika and H. Harima	1357
---	------

Annealing Behavior of Defects in Multiple-Energy Nitrogen Implanted ZnO Bulk Single Crystal K. Kuriyama, K. Matsumoto, M. Ooi and K. Kushida	1361
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